

2SJ325

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} =-30V, V _{GS} =0			-10	μ A
Gate leakage current	I _{GSS}	V _{GS} =±16V, V _{BS} =0			±10	μ A
Gate cut-off voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.0	-1.5	-2.0	V
Forward transfer admittance	Y _{fs}	V _{DS} =-10V, I _D =-2.0A	3.0	4.2		S
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-2.0A		0.18	0.11	Ω
		V _{GS} =-4V, I _D =-1.6A		0.15	0.24	Ω
Input capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0, f=1MHZ		800		pF
Output capacitance	C _{oss}			600		pF
Reverse transfer capacitance	C _{rss}			250		pF
Turn-on delay time	t _{d(on)}	V _{GS(on)} =-10V, V _{DD} =-15V, I _D =-2A R _L =7.5Ω, R _G =10Ω		15		ns
Rise time	t _r			65		ns
Turn-off delay time	t _{d(off)}			85		ns
Fall time	t _f			60		ns
Total Gate Charge	Q _g	V _{GS} =-10V, I _D =-4.0A, V _{DD} =-24V		28		nC
Gate to Source Charge	Q _{GS}			3		nC
Gate Drain Charge	Q _{GD}			11		nC
Body Diode Forward Voltage	V _F	I _F =4.0A, V _{GS} =0		0.9		V
Reverse Recovery time	t _{rr}	I _F =4.0A, V _{GS} =0, di/dt=50A/μ s		65		ns
Reverse Recovery Charge	Q _{rr}			60		nC